Powerking Electronics (ShenZhen) Co., LTD.

深圳市柏健電子有限公司

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SPCEIFICATION FOR APPROVER

客户名称 (Customer Name)	迈科科技有限公司
日 期 (Date)	2008-04-10
品 牌(Brand)	BCD
型 号(Parts No)	AZ7500CM-E1
客户签章(Customer's Signatu	ıre)
全部承认(Pull Approved)	Const 1 - North
日 期(Date)	17/a-08



Data Sheet

AZ7500B/C

PULSE-WIDTH-MODULATION CONTROL CIRCUITS

Features

General Description

marily for power supply control lation switching regulator control circuit designed pri-The AZ7500B/C is a voltage mode pulse width modu-

voltage regulation. The AZ7500B/C provides for push-pull or single-ended output operation, which can be cision of voltage reference (V_{REF}) is improved up to \pm control flip-flop, and an output control circuit. The preselected through the output control 1% through trimming and this provides a better output two error amplifiers, an on-chip adjustable oscillator, a dead-time control (DTC) comparator, a pulse-steering The AZ7500B/C consists of a reference voltage circuit

they have 4.95V and 5V reference voltage respectively The difference between AZ7500B and AZ7500C is that

Applications

DIP-16 and SOIC-16 The AZ7500B/C is available in standard packages of

Charger SMPS Back Light Inverter

- Stable 4.95V/5V Reference Voltage Trimmed to ±1.0% Accuracy
- Uncommitted Output TR for 200mA Sink or Source Current
- Output Control Single-End or Push-Pull Operation Selected by
- Internal Circuitry Prohibits Double Pulse at Either
- Output Complete PWM Control Circuit with Variable
- On-Chip Oscillator with Master or Slave Opera Duty Cycle
- tion



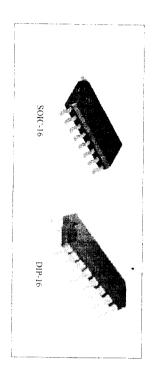


Figure 1. Package Types of AZ7500B/C

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PULSE-WIDTH-MODULATION CONTROL CIRCUITS

AZ7500B/C Data Sheet

Pin Configuration

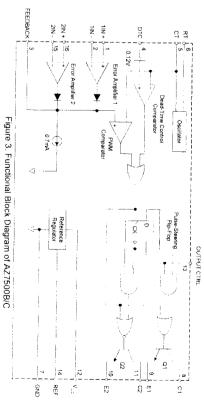
PEEDBACK 3 DTC 4 CT 5 RT 6 ž GND 9 (SOIC-16/DIP-16) M/P Package E2 E 2 REF ☐ 2IN-· V_{CC} OUTPUT CTRL 2jN +

Figure 2. Pin Configuration of AZ7500B/C (Top View)

Output Function Control Table

$V_I = V_{REF}$		V _I = CiND	Signal for Output Control	
 Normal push-pull operation	the state of the s	Single-ended or parallel output	Output Function	

Functional Block Diagram



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Ordering Information PULSE-WIDTH-MODULATION CONTROL CIRCUITS

AZ7500B/C

Data Sheet

Reference Voltage B: 4,95V C 5.0V AZ7500 🗆 🗆 - 🗆 Package M: SOIC-16 P: DIP-16 E1: Lead Free Blank. Tin Lead TR: Tape and Reel Blank: Tube

Package	Temperature	Pan	Part Number	Mari	Marking ID	
	Kange	Yin Lead	Lead Free	Tin Lead	Lead Free	Packing Type
	-		-		The second of the second	
	•	AZ7500BM	AZ7500BM: E1	AZ7500BM	AZ7500BM-E1	Tube
SOIC-16		AZ7500BMTR	AZ7500BMTR-FI	477500DM	173600	
3OIC-16		N THEODOR	AZ NOOBMIK-EI AZ 7500BM	AZ7500BM	AZ7500BM-E1	Tape & Reel
	-40 to 85°C	W 2000 W	AZ7500CM-E1	AZ7500CM	AZ7500CM-F)	7
		AZZSOOCATE	A 775.000			0.000
		MIN SOUTH	AZ7500CM		AZ7500CM-E1	Tape & Reel
		4775/mpp				
DIP-16		AC. / SOUBP	AZ7500BP-E1	AZ7500BP	AZ7500BP-E1	Tube
		4.2.55(MAI)				
		ACCOUNT P	AZ7SD(CP.E)	AZ7500CP	AZ7500CP-E1	Tube

BCD Semiconductor's Ph-free products, as designated with "E1" suffix in the part number, are RoHS compliant

PULSE-WIDTH-MODULATION CONTROL CIRCUITS

AZ7500B/C

Data Sheet

Absolute Maximum Ratings (Note 1)

B				
ranameter	Symbol		Value	Unit
Supply Voltage (Note 2)	Vec		40	V
Amplifier Input Voltage	Ŋ	-0.3 10	-0.3 to V _{CC} + 0.3	<
Collector Output Voltage	Y.		40	
The sounds	Ýo		40	V
Collector Output Current	Io		250	mA
Package Thennal Impedance	Z	M Package	7.3	
(Access)	Ā	P Package	67	°C/W
Lead Temperature 1.6mm from case for 10 seconds			260	λο
Storage Temperature Range	T_{STG}	-65	-65 to 150	J.ºC
ESD rating (Machine Model)			200	<
No. 1 G				

Ratings"for extended periods may affect device reliability.

Note 2: All voltage values are with respect to the network ground terminal.

Note 3: Maximum power dissipation is a function of T₁(max), R_{0,A} and T_A. The maximum allowable power dissipations are function of T₁(max). Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum."

of 150°C can affect reliability. pation at any allowable ambient temperature is $P_{\mathbf{D}}$: $(T_j(max) \cdot T_A \ \mathcal{V}R_{0JA})$. Operating at the absolute maximum T_j

Recommended Operating Conditions

r at atticier	Symbol	Min	Typ	May	
Supply Voltage	Ver	7	5	2,	3
Collector Output Voltage				30	<
2 Surrey and and	VCI, VC2		30	36	۷
Collector Output Current (Each Transistor)	l _{C1} , l _{C2}			200	mA .
Amplifier Innut Voltage					
affine upor votage	_<	0.3		V _{CC} -2	<
Current Into Feedback Terminal	I _{FB}			0.3	3
Reference Output Current					2,1114
	\REF			10	mA
timing Capacitor	C _T	0.00047	100.0	10	Ę
fiming Resistor	₽.	1.8	30	400	
Oscillator Frequency	5				72.
	lose	1.0	40	200	ZHZ
PWM Input Voltage (Pin 3, 4, 14)		0.3			
Operating Free-Air Temperature	T _A	40	-	88	

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PULSE-WIDTH-MODULATION CONTROL CIRCUITS

Data Sheet AZ7500B/C

Electrical Characteristics $T_{A} \approx 25^{o}C, \ V_{CC} \approx 20V, \ f \approx 10 KHz \ unless \ otherwise \ noted.$

Parameter	Symbol	Conditions	Z.		Max	I air
Reference Section		the second secon				
Output Reference Voltage	V _{KEF}	l _{REF} =lmA	4.90	4.95	5.0	<
W (M. COOD)		$I_{RLF}=1mA$, $T_A=-40$ to $85^{\circ}C$	4.85	4.95	5.05	<
Output Reference Voltage	V_{REF}	I _{REF} =1mA	4.95	50	5.05	<
2000		l _{REF} =1mA, T _A =-40 to 85°C	4.9	5.0	5 -	<
Line Regulation	RLINE	$V_{CC} = 7V$ to 36V		2	25	mV
Load Regulation	RLOAD	IREF-IMA to 10mA		-	15	DIV
Short-Circuit Output Current	NS.	$V_{RE} = 0V$	10	35	50	mA
Oscillator Section						
		$C_{T}=0.001\mu F, R_{T}=30K\Omega$		40		
Oscillator Frequency	fosc	$C_{1}=0.01 \mu F, R_{1}=12 K\Omega$	9.2	10	10.8	K 11.7
	;	C_1 =001 μ F, R_7 =12K Ω , T_{Λ} = -40 to 85 $^{\circ}$ C	9.0		12	
Frequency Change with Temperature	Δf/ΔT	C _T =0.01μF, R _T =12KΩ T _A = -40			-	
		to 85°C				Ş.,
Dead-Lime Control Section						
	SVIG.	ACT'S 00 0 - 14 (4 CF CF CF)		<u> </u>	10	μĀ
Maximum Duty Cycle	D(MAX)	V _{CC} =15V, V4≈ 0V, Pin 13= V _{KBF}	45			ò
Input Threshold Voltage	V	Zero Duty Cycle		w	3	
	1111	Maximum Duty Cycle	0			<
Error-Amplifier Section		7300				
Input Offset Voltage	V ₁₀	V3 = 2.5V		2	10	νm
Input Offset Current	lω	V3 = 2 5V		25	250	nA
Input Bias Current	JBIAS	V3 = 2.5V		0.2	-	μA
Common-Mode Input Voltage Range	V_{CM}	V _{CC} =7V to 36V	-0.3	\perp	V _{CC} -2	<
Open-Loop Voltage Gain		V _O =0.5V to 3.5V	70	95		₽
Unity-Gain Bandwidth	ВW			650		ZE.
Common-Mode Rejection Ratio	CMRR		8;	8 —∔	_	8
Output Sink Current (Feedback)	JSINK	V _{ID} = -15mV to -5V, V3 = 0.7V	-0.3	-0.7		mA
Output Source Current (Feedback)	SOURCE	V _{JD} =15mV to 5V V3 = 3.5V	13	-		mA

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PULSE-WIDTH-MODULATION CONTROL CIRCUITS

rameter Symbol Conditions Min Typ Max Unit
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Data Sheet AZ7500B/C

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
PWM Comparator Section	ă				1		
Input Threshold Voltage		V _{IIH}	Zero duty cycle		4	4.5	<
Input Sink Current		LSINK	V3 = 0.7V	-0.3	-0.7		m A
Output Section				-			
Output Saturation Voltage	Common Emitter	V _{CE} (SAT)	$V_{\rm E} = 6 \text{V}$. $I_{\rm C} = 200 \text{mA}$		=	1.3	
Cubut Saturation voltage	Emitter	Vec	V _{CC} = 15V,				<
	Follower	(SAT)	$l_{j} = -200 \text{mA}$		1.5	2.5	
Collector Off-State Current		I _C (OFF)	V _{CE} = 36V, V _{CC} =36V		2	100	Ā
Emitter Off-State Current		l _E (OFF)	$V_{CC} = V_C = 36V, V_E = 0$			-100	EA.
Total Device					İ		ij
Supply Current		Icc	Pm 6 - V _{REF} , V _{CC} =15V		6	10	mA
Output Switching Characteristics	teristics						
Risc Time		R	Common Emitter Common Collector		100	200	ns
Fall Time		Ŧ.	Common Emitter Common Collector		25	100	ns

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Data Sheet

PULSE-WIDTH-MODULATION CONTROL CIRCUITS

Parametr Measurement information

PEEDBACK 2 1 1 1 N + Test Circuit

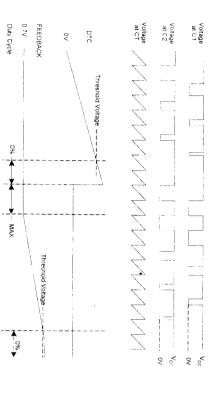


Figure 4. Operational Test Circuit and Waveforms

Voltage Waveforms

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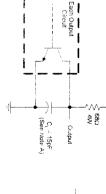
PULSE-WIDTH-MODULATION CONTROL CIRCUITS

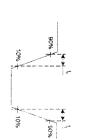
Data Sheet

Parametr Measurement information (Continued)

V, Amplifier Under Test

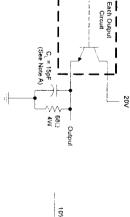
Figure 5. Error Amplifier Characteristics

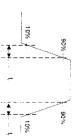




Note A: C_L includes probe and jig capacitance.

Figure 6. Common-Emitter Configuration





Note A: C_L includes probe and jig capacitance. Figure 7. Emitter-Follower Configuration

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PULSE-WIDTH-MODULATION CONTROL CIRCUITS

Data Sheet

Typical Performance Characteristics

f - Oscillator Frequency (Hz) 100k 10k 10k RT - Timing Resistance (£2) V_{cc}=20V T_A=25°C 0.001µF

Figure 8. Oscillator Frequency vs. RT and CT

Voltage Gain (dB) 100 Frequency (Hz) îDk . V_{cc}=20V ...V_c=3V T_k=25°C 100k

Figure 9. Error Amplifier Small-Signal Voltage Gain vs. Frequency

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Typical Applications PULSE-WIDTH-MODULATION CONTROL CIRCUITS

AZ7500B/C

Data Sheet

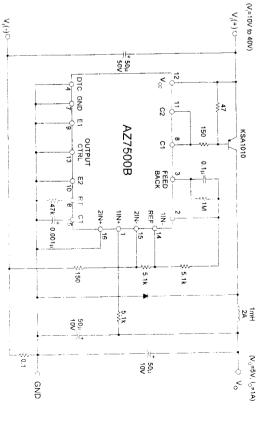


Figure 10. Pulse Width Modulated Step-Down Converter

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Mechanical Dimensions PULSE-WIDTH-MODULATION CONTROL CIRCUITS

AZ7500B/C

Data Sheet

SOIC-16

Unit: mm(inch)

Φ 2.000(0.079)
Depth 0.060(0.002)
0.100(0.004) 0.203(0.008) 1.300(0.051) 3.940(0.155) 6.040(0.238) 0 1.000(0.039) 1.650(0.065) П 0.406(0.016) 1.270(0.050 10.000(0.394) 0.150(0.006) 0.700(0.028) 0.250(0.010) 70 20:1 0.250(0.010) 0.200(0.008)MIN 50-C 0.500(0.020) R0.200(0.008) R0.200(0.008) 2 1 -3

S \$\phi_1.000(0.039)

Depth 0.200(0.008) 0.200(0.008) 1.000(0.039)

8 20:1

Ċ

0.400(0.016)×45

DIP-16

Mechanical Dimensions (Continued) PULSE-WIDTH-MODULATION CONTROL CIRCUITS

AZ7500B/C Data Sheet

Unit: mm(inch)

0.560(0.014) R0.750(0.030) 16.800(0.740) 19.200(0.756) 2 540(0.100) 0.510(0.020)MIN 3.710(0.146) 4.310(0.170) 3.600(0.118) 6 200(0.244) 6 600(0.260) 8 200(0 323) 9 400(0 370) 0.204(0.008) 4: 3:000(0:118) Depth 0.150(0.002) 0.150(0.006) 0.700(0,028) 3.200(0.126) 3.500(0.142)

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No. SH7042944/CHEM

Date: Apr. 27, 2007

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JIANGSU CHANGJIANG ELECTRONIC TECHNOLOGY CO., LTD 78, CHANGSHAN RD, JIANGYIN, JIANGSU CHINA

The following sample(s) was/were submitted and identified by/on behalf of the client as:

Sample Name

: SOP PACKAGE PART (INCLUDE SOP16/28)

SGS Ref No.

: 10333677-7

Model

: SOP (INCLUDE SOP16/28)

Sample Receiving Date: Apr.24, 2007

Testing Period

: Apr.24 - Apr.27, 2007

Test Requested

: (1) In accordance with the RoHS Directive 2002/95/EC, and its amendment directives

(2) To determine the PCBs (Polychlorinated Biphenyls) content of the submitted

sample.

(3) To determine the Polychlorinated Naphthalene content of the submitted sample.

(4) To determine the Short Chain Chlorinated Paraffin content of the submitted

sample.

Test Method

: (1-1) With reference to IEC 62321 Ed.1 111/54/CDV for Cadmium content.

Analysis was performed by ICP.

(1-2) With reference to IEC 62321 Ed.1 111/54/CDV for Lead content.

Analysis was performed by ICP.

(1-3) With reference to IEC 62321 Ed.1 111/54/CDV for Mercury content.

Analysis was performed by ICP.

(1-4) With reference to IEC 62321 Ed.1 111/54/CDV for Hexavalent Chromium by

Colorimetric Method.

(1-5) With reference to IEC 62321 Ed.1 111/54/CDV for PBBs / PBDEs content.

Analysis was performed by GC/MS.

(2) With reference to US EPA 8082, Analysis was performed by GC-MS.

(3) With reference to US EPA 8081, Analysis was performed by GC-MS.

(4) With reference to US EPA 8081, Analysis was performed by GC/MS.

Test Results

: Please refer to next pages

Signed for and on behalf of SGS-CSTC Chemical Laboratory

> Ella Zhang Sr. Section Head

Signed for and on behalf of SGS-CSTC Chemical Laboratory

> Sandy Hao Lab Manager



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Date: Apr. 27, 2007

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Test results by chemical method

(1) Cadmium, Lead, Mercury, Hexavalent Chromium, PBBs(Polybrominated biphenyls) PBBEs(PBDEs) (Polybrominated biphenyl ethers) content(Unit: mg/kg)

(Folybrottlinated biphenyl ethers) con				icityis) i L
Test Item(s):	Method (refer to)	1*	MDL	RoHS Limit
Cadmium(Cd)	(1-1)	ND	2	100
Lead (Pb)	(1-2)	11	2	
Mercury (Hg)	(1-3)	ND	2	1000
Hexavalent Chromium (CrVI)	(1-4)	ND	2	1000
Sum of PBBs	(, 4)	ND		1000
Monobromobiphenyl	•	ND	-	1000
Dibromobiphenyl		ND	5	
Tribromobiphenyl			5	-
Tetrabromobiphenyl		ND	5	-
Hexabromobiphenyl		ND	5	-
Pentabromobiphenyl		ND	5	-
Heptabromobiphenyl		ND	5	-
Octabromobiphenyl		ND	5	
Nonabromobiphenyl		ND	5	-
Decabromobiphenyl		ND	5	-
Sum of PBDEs (Note 4)	(4.5)	ND	5	-
Monobromodiphenyl ether	(1-5)	ND	-	1000
Dibromodiphenyl ether		ND	5	-
Tribromodiphenyl ether		ND	5	-
Tetrabromodiphenyl ether		ND	5	
Pentabromodiphenyl ether		ND	5	_
Hexabromodiphenyl ether		ND	5	-
Heptabromodiphenyl ether		ND	5	-
Octabromodiphenyl ether		ND	5	_
Nonabromodiphenyl ether		ND	5	_
Decabromodiphenyl ether		ND	5	-
Sum of PBDEs (Mono to Deca)		ND	5	
Som of Labes (Motio to Deca)		ND	-	-





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(2)~(4) PCBs (Polychlorinated Biphenyls) content ,Polychlorinated Naphthalene content and Short Chain Chlorinated Paraffin content (Unit: mg/kg)

Test Item(s):	Method (refer to)	1*	MDL
PCBs (Polychlorinated Biphenyls) content	Trefer (O)		-
2.4.4 - Trichlorobiphenyl (PCB 28) CAS 7012-37-5	1	ND	0.5
2.2'.5.5'-Tetrachloro-biphenyl (PCB 52) CAS 35693-99-3	1	ND	0.5
2.2'.4.5.5'-Pentachloro-biphenyl (PCB 101) CAS 37680-73-2		ND	0.5
2.3'.4.4'.5-Pentachlorobiphenyl (PCB 118) CAS 31508-00-6	(2)	ND	0.5
2.2'3.4.4'.5'-Hexachloro-biphenyl (PCB 138) CAS 35065-28-2		ND	0.5
2.2'.4.4'.5.5'-Hexachloro-biphenyl (PCB 153) CAS 35065-27-1		ND	0.5
2.2'.3.4.4'.5.5'-Heptachlorobiphenyl (PCB 180) CAS 35065-29-3		ND	0.5
olychlorinated Naphthalene content			0.5
2-Chlorinated Naphthalene	-	ND	5
1,4-Dichlorinated Naphthalene	-	ND	5
1,5-Dichlorinated Naphthalene	-	ND	
1,2-Dichlorinated Naphthalene	(3)		5
1,8-Dichlorinated Naphthalene		ND	5
		ND	5
1,2,3,4-Tetrachlorinated Naphthalene		ND	5
Octa-chlorinaed Naphthalene		ND	5
ort Chain Chlorinated Paraffin	(4)	ND	30

Test Part Description:

1. Black body part (mix all)

Note:

- (1) mg/kg = ppm
- (2) ND = Not Detected
- (3) MDL = Method Detection Limit
- (4) Sum of Mono to NonaBDE & according to 2005/717/EC DecaBDE is exempt.
- (5) "-" = Not Regulated
- (6) The maximum permissible limit is quoted from the document 2005/618/EC amending RoHS directive 2002/95/EC
- (7) * The sample(s) was analyzed on behalf of the applicant as mixing whole/part sample in one testing. The result(s) in report means average of whole sample. The result(s) will be different obviously if the sample(s) was tested as requirement of RoHS, and result(s) may be higher than that of report. The applicant will take the responsibility of all discrepancy and risk.

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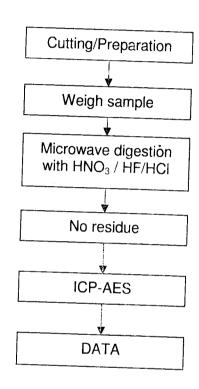
No. SH7042944/CHEM

Date: Apr. 27, 2007

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ATTACHMENTS

Cd and Pb Measurement Flowchart



The samples were dissolved totally by pre-conditioning method according to above flow chart.

Tested by Checked by : Chaven Lian : Terry Wang



No. SH7042944/CHEM

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Sample photo:



SGS authenticate the photo on original report only

*** End of Report ***